3.3 V ECL 2-Input Differential AND/NAND

MC100LVEL05

ON Semiconductor®

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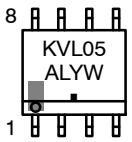


SOIC−8
D SUFFIX
CASE 751

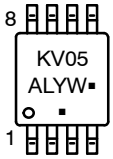


TSSOP−8
DT SUFFIX
CASE 948R

MARKING DIAGRAMS*



SOIC−8



TSSOP−8

A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

Description

The MC100LVEL05 is a 2-input differential AND/NAND gate. The device is functionally equivalent to the MC100EL05 device and operates from a 3.3 V supply voltage. With propagation delays and output transition times equivalent to the EL05, the LVEL05 is ideally suited for those applications which require the ultimate in AC performance at low voltage power supplies.

Because a negative 2-input NAND is equivalent to a 2-input OR function, the differential inputs and outputs of the device allows the LVEL05 to also be used as a 2-input differential OR/NOR gate.

Features

- 340 ps Propagation Delay
- High Bandwidth Output Transitions
- ESD Protection:
  - > 4 kV Human Body Mode
  - > 200 V Machine Model
- The 100 Series Contains Temperature Compensation
- PECL Mode Operating Range: V_{CC} = 3.0 V to 3.8 V with V_{EE} = 0 V
- NECL Mode Operating Range: V_{CC} = 0 V with V_{EE} = −3.0 V to −3.8 V
- Internal Input Pulldown Resistors
- Q Output will Default LOW with All Inputs Open or at V_{EE}
- Meets or Exceeds JEDEC Spec EIA/JESD78 IC Latchup Test
- Moisture Sensitivity
  - Level 1 for SOIC−8
  - Level 3 for TSSOP−8
  - For Additional Information, see Application Note AND8003/D
- Flammability Rating: UL 94 V−0 @ 0.125 in, Oxygen Index: 28 to 34
- Transistor Count = 69 Devices
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

ORDERING INFORMATION

Device	Package	Shipping†
MC100LVEL05DG	SOIC−8 (Pb-Free)	98 Units/Tube
MC100LVEL05DR2G	SOIC−8 (Pb-Free)	2500/Tape & Reel
MC100LVEL05DTR2G	TSSOP−8 (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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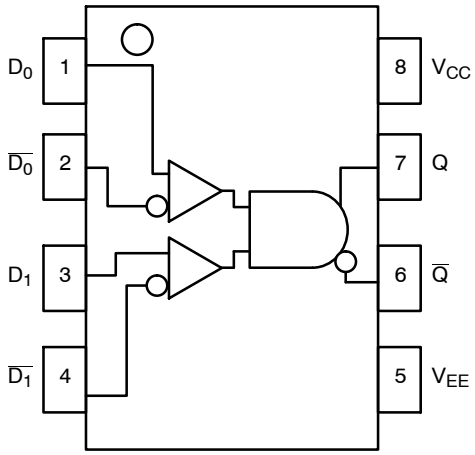


Figure 1. Logic Diagram and Pinout Assignment

Table 1. PIN DESCRIPTION

PIN	FUNCTION
D0, $\overline{D0}$; D1, $\overline{D1}$	ECL Data Inputs
Q, $\overline{Q}$	ECL Data Outputs
V_{CC}	Positive Supply
V_{EE}	Negative Supply

Table 2. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	PECL Mode Psower Supply	V_{EE} = 0 V		8 to 0	V
V_{EE}	NECL Mode Power Supply	V_{CC} = 0 V		−8 to 0	V
V_I	PECL Mode Input Voltage NECL Mode Input Voltage	V_{EE} = 0 V V_{CC} = 0 V	$V_I \le V_{CC}$ $V_I \ge V_{EE}$	6 to 0 −6 to 0	V
I_{out}	Output Current	Continuous Surge		50 100	mA
T_A	Operating Temperature Range			−40 to +85	°C
T_{stg}	Storage Temperature Range			−65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC−8	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC−8	41 to 44 ±5%	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP−8	185 140	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP−8	41 to 44 ±5%	°C/W
T_{sol}	Wave Solder (Pb-Free)	< 2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 3. LVPECL DC CHARACTERISTICS (V_{CC} = 3.3 V; V_{EE} = 0.0 V (Note 1))

		−40°C			25°C			85°C			
Symbol	**Characteristic**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Unit**
I_{EE}	Power Supply Current		18	25		18	25		19	26	mA
V_{OH}	Output HIGH Voltage (Note 2)	2215	2295	2420	2275	2345	2420	2275	2345	2420	mV
V_{OL}	Output LOW Voltage (Note 2)	1470	1605	1745	1490	1595	1680	1490	1595	1680	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	2135		2420	2135		2420	2135		2420	mV
V_{IL}	Input LOW Voltage (Single-Ended)	1490		1825	1490		1825	1490		1825	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential) (Note 3) Vpp < 500 mV Vpp ≥ 500 mV	 1.2 1.5		 2.9 2.9	 1.1 1.4		 2.9 2.9	 1.1 1.4		 2.9 2.9	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary ±0.3 V.
2. Outputs are terminated through a 50 ohm resistor to V_{CC} − 2.0 V.
3. V_{IHCMR} min varies 1:1 with V_{EE}, max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP}min and 1 V.

Table 4. LVNECL DC CHARACTERISTICS (V_{CC} = 0.0 V; V_{EE} = −3.3 V (Note 1))

		−40°C			25°C			85°C			
Symbol	**Characteristic**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Unit**
I_{EE}	Power Supply Current		18	25		18	25		19	26	mA
V_{OH}	Output HIGH Voltage (Note 2)	−1085	−1005	−880	−1025	−955	−880	−1025	−955	−880	mV
V_{OL}	Output LOW Voltage (Note 2)	−1830	−1695	−1555	−1810	−1705	−1620	−1810	−1705	−1620	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	−1165		−880	−1165		−880	−1165		−880	mV
V_{IL}	Input LOW Voltage (Single-Ended)	−1810		−1475	−1810		−1475	−1810		−1475	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential) (Note 3) Vpp < 500 mV Vpp ≥ 500 mV	 −2.1 −1.8		 −0.4 −0.4	 −2.2 −1.9		 −0.4 −0.4	 −2.2 −1.9		 −0.4 −0.4	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary ±0.3 V.
2. Outputs are terminated through a 50 ohm resistor to V_{CC} − 2.0 V.
3. V_{IHCMR} min varies 1:1 with V_{EE}, max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP}min and 1 V.

Table 5. AC CHARACTERISTICS (V_{CC} = 3.3 V; V_{EE} = 0.0 V or V_{CC} = 0.0 V; V_{EE} = −3.3 V (Note 1))

		−40°C			25°C			85°C			
Symbol	**Characteristic**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Unit**
f_{max}	Maximum Toggle Frequency		1.6			1.6			1.6		GHz
t_{PLH} t_{PHL}	Propagation Delay to Output	240	260	440	240	340	440	250		450	ps
t_{JITTER}	Cycle-to-Cycle Jitter		6.7			7.5			8.2		ps
V_{PP}	Input Swing (Note 2)	150		1000	150		1000	150		1000	mV
t_r t_f	Output Rise/Fall Times Q (20% − 80%)	100		320	100	210	320	100		320	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. V_{EE} can vary ±0.3 V.
2. V_{PP}(min) is the minimum input swing for which AC parameters are guaranteed. The device has a DC gain of ≈40.

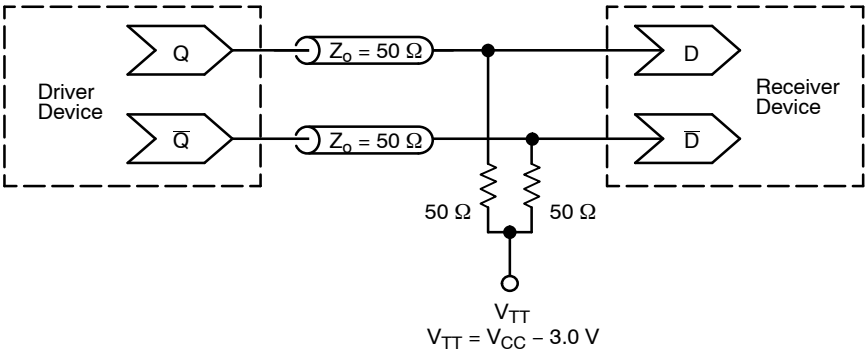


Figure 2. Typical Termination for Output Driver and Device Evaluation (See Application Note AND8020/D − Termination of ECL Logic Devices.)

Resource Reference of Application Notes

AN1405/D − ECL Clock Distribution Techniques

AN1406/D − Designing with PECL (ECL at +5.0 V)

AN1503/D − ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D − Metastability and the ECLinPS Family

AN1568/D − Interfacing Between LVDS and ECL

AN1672/D − The ECL Translator Guide

AND8001/D − Odd Number Counters Design

AND8002/D − Marking and Date Codes

AND8020/D − Termination of ECL Logic Devices

AND8066/D − Interfacing with ECLinPS

AND8090/D − AC Characteristics of ECL Devices

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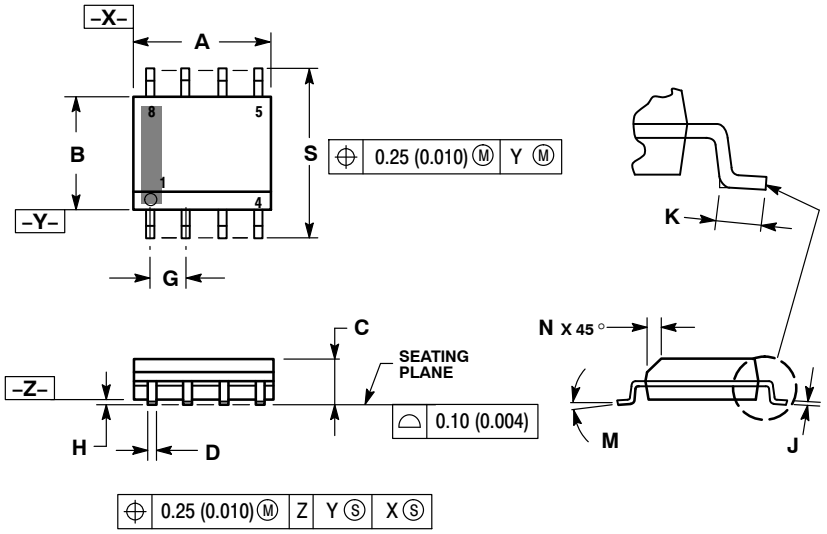
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SCALE 1:1

SOIC−8 NB
CASE 751−07
ISSUE AK

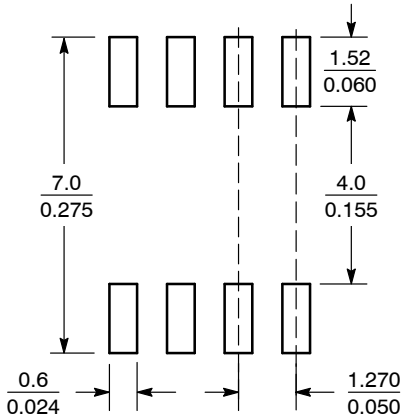
DATE 16 FEB 2011



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

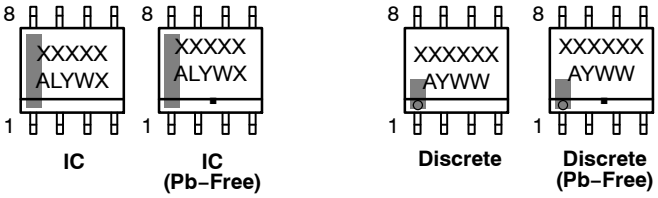
SOLDERING FOOTPRINT*



SCALE 6:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



IC | IC (Pb−Free) | Discrete | Discrete (Pb−Free)

XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SOIC−8 NB
CASE 751−07
ISSUE AK

DATE 16 FEB 2011

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. COLLECTOR
4. EMITTER
5. EMITTER
6. BASE
7. BASE
8. EMITTER

STYLE 2:
PIN 1. COLLECTOR, DIE, #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. BASE, #2
6. EMITTER, #2
7. BASE, #1
8. EMITTER, #1

STYLE 3:
PIN 1. DRAIN, DIE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. GATE, #2
6. SOURCE, #2
7. GATE, #1
8. SOURCE, #1

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
7. ANODE
8. COMMON CATHODE

STYLE 5:
PIN 1. DRAIN
2. DRAIN
3. DRAIN
4. DRAIN
5. GATE
6. GATE
7. SOURCE
8. SOURCE

STYLE 6:
PIN 1. SOURCE
2. DRAIN
3. DRAIN
4. SOURCE
5. SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 7:
PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

STYLE 8:
PIN 1. COLLECTOR, DIE #1
2. BASE, #1
3. BASE, #2
4. COLLECTOR, #2
5. COLLECTOR, #2
6. EMITTER, #2
7. EMITTER, #1
8. COLLECTOR, #1

STYLE 9:
PIN 1. EMITTER, COMMON
2. COLLECTOR, DIE #1
3. COLLECTOR, DIE #2
4. EMITTER, COMMON
5. EMITTER, COMMON
6. BASE, DIE #2
7. BASE, DIE #1
8. EMITTER, COMMON

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT
4. GROUND
5. GROUND
6. BIAS 2
7. INPUT
8. GROUND

STYLE 11:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 12:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 14:
PIN 1. N−SOURCE
2. N−GATE
3. P−SOURCE
4. P−GATE
5. P−DRAIN
6. P−DRAIN
7. N−DRAIN
8. N−DRAIN

STYLE 15:
PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

STYLE 16:
PIN 1. EMITTER, DIE #1
2. BASE, DIE #1
3. EMITTER, DIE #2
4. BASE, DIE #2
5. COLLECTOR, DIE #2
6. COLLECTOR, DIE #2
7. COLLECTOR, DIE #1
8. COLLECTOR, DIE #1

STYLE 17:
PIN 1. VCC
2. V2OUT
3. V1OUT
4. TXE
5. RXE
6. VEE
7. GND
8. ACC

STYLE 18:
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 19:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

STYLE 20:
PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3
4. CATHODE 4
5. CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 22:
PIN 1. I/O LINE 1
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 23:
PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 24:
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

STYLE 25:
PIN 1. VIN
2. N/C
3. REXT
4. GND
5. IOUT
6. IOUT
7. IOUT
8. IOUT

STYLE 26:
PIN 1. GND
2. dv/dt
3. ENABLE
4. ILIMIT
5. SOURCE
6. SOURCE
7. SOURCE
8. VCC

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 28:
PIN 1. SW_TO_GND
2. DASIC_OFF
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

STYLE 29:
PIN 1. BASE, DIE #1
2. EMITTER, #1
3. BASE, #2
4. EMITTER, #2
5. COLLECTOR, #2
6. COLLECTOR, #2
7. COLLECTOR, #1
8. COLLECTOR, #1

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
3. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
6. SOURCE 1/DRAIN 2
7. SOURCE 1/DRAIN 2
8. GATE 1

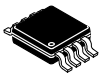
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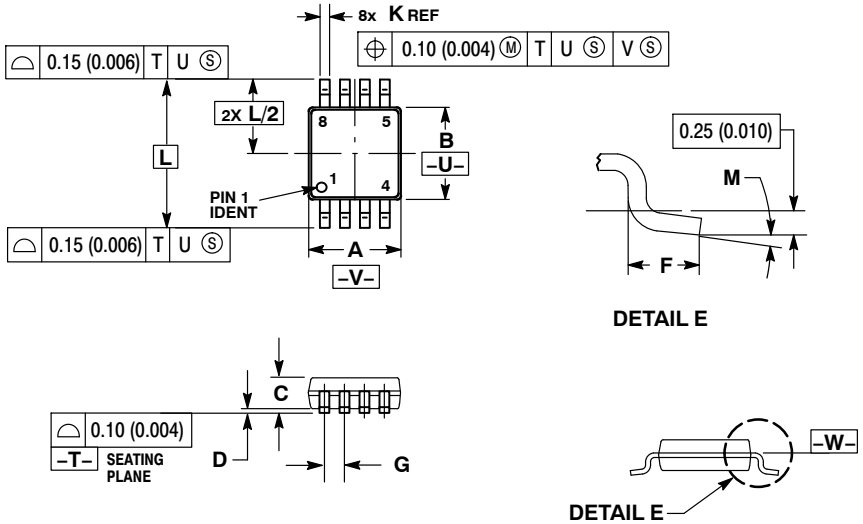
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TSSOP 8
CASE 948R–02
ISSUE A

DATE 04/07/2000



SCALE 2:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
M	0°	6°	0°	6°

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